

MOS FIELD EFFECT TRANSISTOR

2SJ602

SWITCHING P-CHANNEL POWER MOS FET INDUSTRIAL USE

DESCRIPTION

The 2SJ602 is P-channel MOS Field Effect Transistor designed for solenoid, motor and lamp driver.

FEATURES

• Super low on-state resistance:

$$\begin{split} R_{DS(on)1} &= 73~m\Omega~MAX.~(V_{GS} = -10~V,~I_{D} = -10~A) \\ R_{DS(on)2} &= 107~m\Omega~MAX.~(V_{GS} = -4.0~V,~I_{D} = -10~A) \end{split}$$

- Low Ciss: Ciss = 1300 pF TYP.
- Built-in gate protection diode

ORDERING INFORMATION

PART NUMBER	PACKAGE
2SJ602	TO-220AB
2SJ602-S	TO-262
2SJ602-ZJ	TO-263
2SJ602-Z	TO-220SMD ^{Note}

Note TO-220SMD package is produced only in Japan

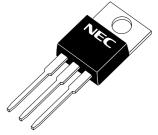
ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vos = 0 V)	VDSS	-60	V
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	∓20	V
Drain Current (DC) (Tc = 25°C)	I _{D(DC)}	∓20	Α
Drain Current (pulse) Note1	ID(pulse)	∓50	Α
Total Power Dissipation (Tc = 25°C)	Рт	40	W
Total Power Dissipation (T _A = 25°C)	Рт	1.5	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	-20	Α
Single Avalanche Energy Note2	Eas	40	mJ

Notes 1. PW \leq 10 μ s, Duty cycle \leq 1%

2. Starting T_{ch} = 25°C, R_G = 25 Ω , V_{GS} = -20 V \rightarrow 0 V





(TO-262)



(TO-263, TO-220SMD)



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ELECTRICAL CHARACTERISTICS (TA = 25°C)

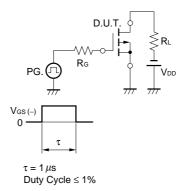
Characteristics	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Zero Gate Voltage Drain Current	Inss	V _{DS} = -60 V, V _{GS} = 0 V			-10	μΑ
Gate Leakage Current	Igss	V _{GS} = ∓20 V, V _{DS} = 0 V			∓10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	1.5	2.0	2.5	V
Forward Transfer Admittance	yfs	V _{DS} = -10 V, I _D = -10 A	8	16		S
Drain to Source On-state Resistance	RDS(on)1	V _G S = -10 V, I _D = -10 A		59	73	mΩ
	RDS(on)2	$V_{GS} = -4.0 V, I_{D} = -10 A$		75	107	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz		1300		pF
Output Capacitance	Coss			240		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-on Delay Time	t _{d(on)}	$I_D = -10 \text{ A}, V_{GS(on)} = -10 \text{ V}, V_{DD} = -30 \text{ V},$		9		ns
Rise Time	tr	$R_G = 0 \Omega$		12		ns
Turn-off Delay Time	t _{d(off)}			54		ns
Fall Time	t f			15		ns
Total Gate Charge	Q _G	$I_D = -20 A$, $V_{DD} = -48 V$, $V_{GS} = -10 V$		26		nC
Gate to Source Charge	Qgs			5		nC
Gate to Drain Charge	Q _{GD}			7		nC
Body Diode Forward Voltage	V _F (S-D)	I _F = -20 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	trr	I _F = -20 A, V _{GS} = 0 V		50		ns
Reverse Recovery Charge	Qrr	$di/dt = -100 A/\mu s$		110		nC

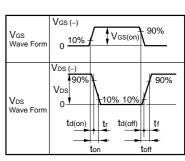
TEST CIRCUIT 1 AVALANCHE CAPABILITY

$V_{GS} = -20 \text{ V} \rightarrow 0 \text{ V}_{m}$ V_{DD} V_{DD} V_{DD} V_{DD} V_{DD} V_{DD} V_{DD} V_{DD} V_{DD} V_{DD}

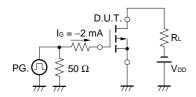
Starting Tch

TEST CIRCUIT 2 SWITCHING TIME





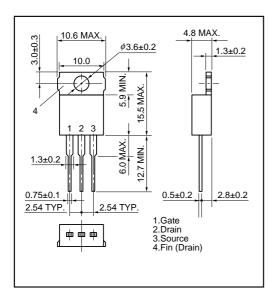
TEST CIRCUIT 3 GATE CHARGE



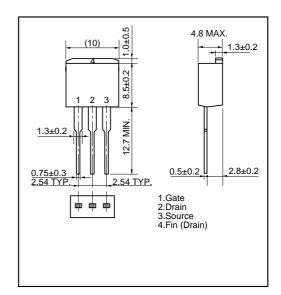


PACKAGE DRAWINGS (Unit: mm)

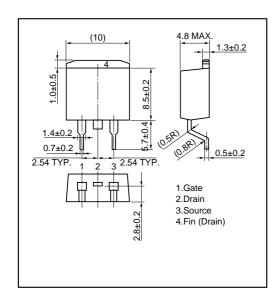
1) TO-220AB(MP-25)



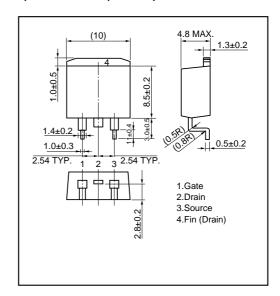
2) TO-262(MP-25 Fin Cut)



3) TO-263 (MP-25ZJ)

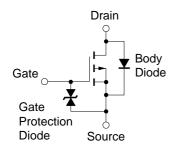


4) TO-220SMD(MP-25Z)^{Note}



Note This Package is produced only in Japan.

EQUIVALENT CIRCUIT



Remark

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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